imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Complementary Power Transistors

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("1" Suffix)
- Electrically Similar to Popular TIP41 and TIP42 Series
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit	
Collector-Emitter Voltage	V _{CEO}	100	Vdc	
Collector-Base Voltage	V _{CB}	100	Vdc	
Emitter-Base Voltage	V _{EB}	5	Vdc	
Collector Current – Continuous	۱ _C	6	Adc	
Collector Current – Peak	I _{CM}	10	Adc	
Base Current	Ι _Β	2	Adc	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W W/°C	
Total Power Dissipation (Note 1) @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	1.75 0.014	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C	
ESD – Human Body Model	HBM	3B	V	
ESD – Machine Model	MM	С	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

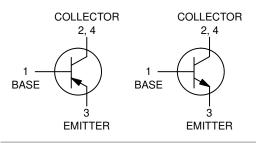


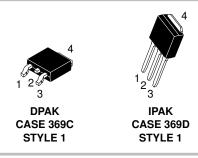
ON Semiconductor®

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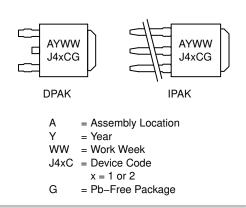
SILICON POWER TRANSISTORS 6 AMPERES 100 VOLTS, 20 WATTS

COMPLEMENTARY





MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	71.4	°C/W

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 3) $(I_{C} = 30 \text{ mAdc}, I_{B} = 0)$	V _{CEO(sus)}	100	-	Vdc
Collector Cutoff Current ($V_{CE} = 60 \text{ Vdc}, I_B = 0$)	ICEO	_	50	μAdc
Collector Cutoff Current ($V_{CE} = 100 \text{ Vdc}, V_{EB} = 0$)	I _{CES}	_	10	μAdc
Emitter Cutoff Current ($V_{BE} = 5$ Vdc, $I_C = 0$)	I _{EBO}	_	0.5	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain ($I_C = 0.3 \text{ Adc}, V_{CE} = 4 \text{ Vdc}$) ($I_C = 3 \text{ Adc}, V_{CE} = 4 \text{ Vdc}$)	h _{FE}	30 15	- 75	-
Collector–Emitter Saturation Voltage $(I_{C} = 6 \text{ Adc}, I_{B} = 600 \text{ mAdc})$	V _{CE(sat)}	_	1.5	Vdc
Base–Emitter On Voltage (I _C = 6 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	-	2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product (Note 4) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc, $f_{test} = 1$ MHz)	fT	3	-	MHz
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1 kHz)	h _{fe}	20	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%. 4. $f_T = |h_{fe}| \bullet f_{test}$.

TYPICAL CHARACTERISTICS

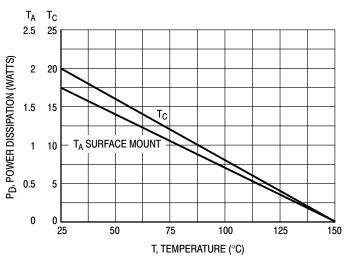


Figure 1. Power Derating

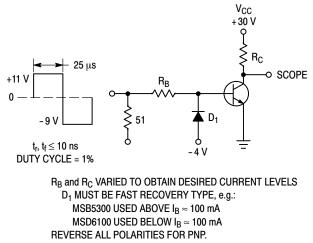


Figure 2. Switching Time Test Circuit

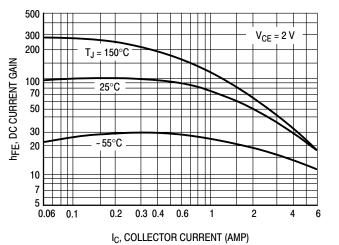


Figure 3. DC Current Gain

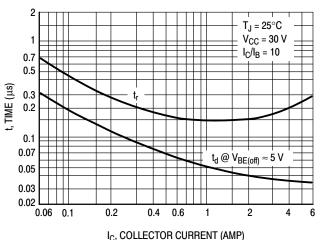
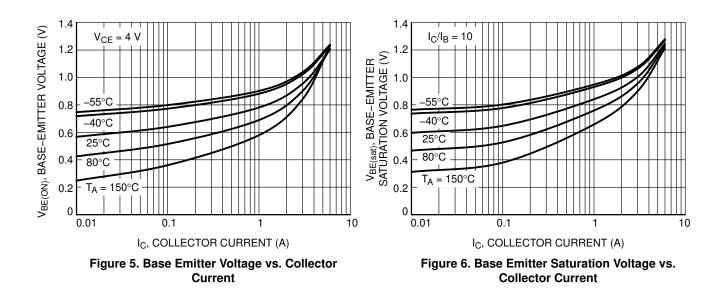


Figure 4. Turn–On Time



TYPICAL CHARACTERISTICS

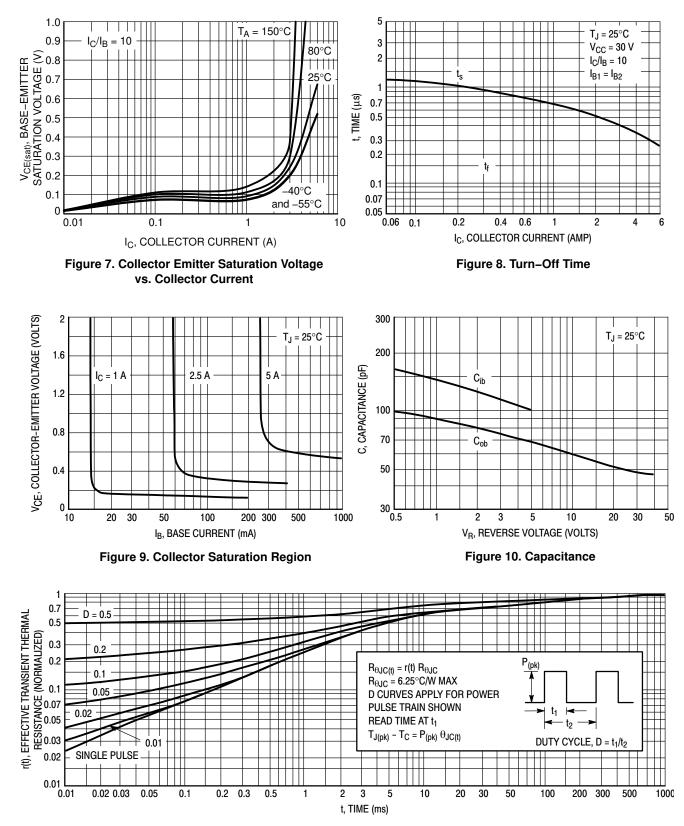


Figure 11. Thermal Response

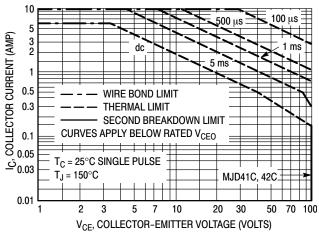


Figure 12. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 12 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 11. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

ORDERING INFORMATION

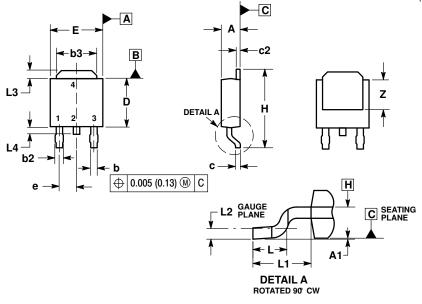
Device	Package Type	Package	Shipping [†]
MJD41CRLG	DPAK (Pb–Free)	369C	1,800 / Tape & Reel
MJD41CT4G	DPAK (Pb–Free)	369C	2,500 / Tape & Reel
NJVMJD41CT4G*	DPAK (Pb–Free)	369C	2,500 / Tape & Reel
MJD42CG	DPAK (Pb–Free)	369C	75 Units / Rail
MJD42C1G	IPAK (Pb–Free)	369D	75 Units / Rail
MJD42CRLG	DPAK (Pb–Free)	369C	1,800 / Tape & Reel
NJVMJD42CRLG*	DPAK (Pb–Free)	369C	1,800 / Tape & Reel
MJD42CT4G	DPAK (Pb–Free)	369C	2,500 / Tape & Reel
NJVMJD42CT4G*	DPAK (Pb–Free)	369C	2,500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE D



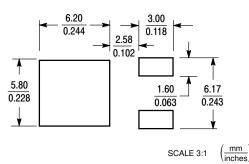
NOTES:

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES. 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-MENSIONS b3, L3 and Z. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE. 5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY. 6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
b	0.025	0.035	0.63	0.89	
b2	0.030	0.045	0.76	1.14	
b3	0.180	0.215	4.57	5.46	
С	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
Е	0.250	0.265	6.35	6.73	
е	0.090 BSC		2.29	BSC	
Н	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.108 REF		2.74	REF	
L2	0.020 BSC		0.51	0.51 BSC	
L3	0.035	0.050	0.89	1.27	
L4		0.040		1.01	
Ζ	0.155		3.93		

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

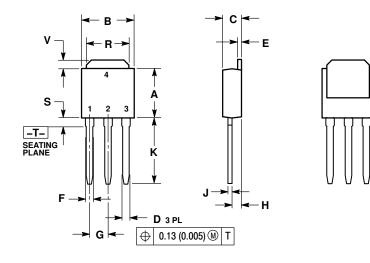
SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

IPAK CASE 369D ISSUE C



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROL LING DIMENSION: INCH

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
Κ	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
z	0.155		3.93	

STYLE 1:

z

PIN 1. BASE 2. COLLECTOR 3. EMITTER

4. COLLECTOR

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